

# **High-Performance Organic Thin-Film Phototransistors Based on Stacked *p-n* Heterojunctions for Enhanced Optoelectronic Response**

Po-Hsiang Fang, Zhao-Lun Kuo, Yu-Tong Wu, Horng-Long Cheng, Wei-Yang Chou\*

Department of Photonics, National Cheng Kung University, Tainan 70101, Taiwan

**Table S1.** XRD diffraction analysis parameters of different semiconductor devices.

	Device_N	Device_P	Device_T
2 $\theta$ (degree)	3.368	5.672	3.33
FWHM (degree)	0.377	0.379	0.466
<i>d</i> -spacing (Å)	26.48	15.58	26.53

**Table S2.** Performances of OTFTs with different semiconducting materials and light irradiance.

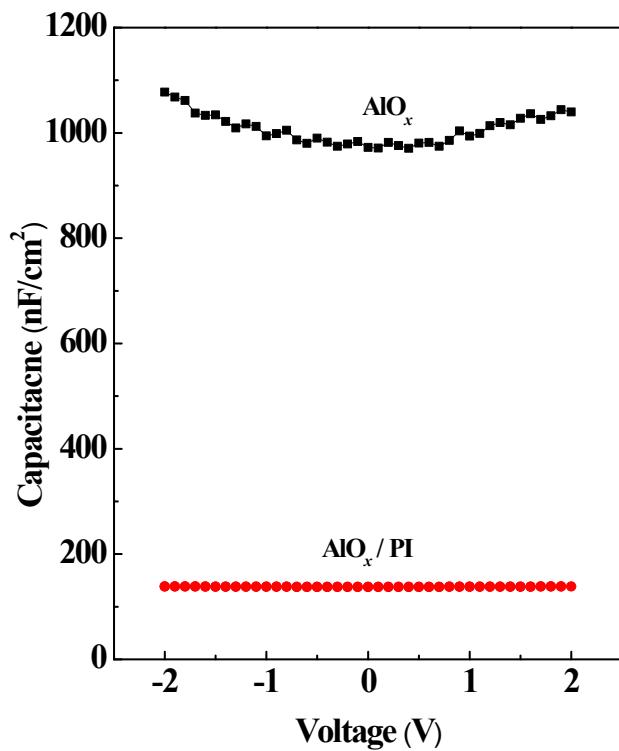
<b>Device</b>	<b>on/off ratio</b>	<b>S.S. (V/dec)</b>	<b><math>V_{TH}</math> (V)</b>	<b>Mobility (cm<sup>2</sup>/Vs)</b>
Device_N (Nonirradiated)	$2.74 \times 10^4$	0.66	0.93	$3.35 \times 10^{-2}$
Device_N (red light)	$4.43 \times 10^4$	0.35	1.09	$3.92 \times 10^{-2}$
Device_N (Nonirradiated)	$1.74 \times 10^4$	0.93	0.62	$2.24 \times 10^{-2}$
Device_N (green light)	$9.77 \times 10^2$	1.95	-0.04	$2.84 \times 10^{-2}$
Device_N (Nonirradiated)	$3.28 \times 10^3$	1.32	0.42	$1.90 \times 10^{-2}$
Device_N (blue light)	$7.19 \times 10^3$	1.08	0.41	$2.55 \times 10^{-2}$
Device_P (Nonirradiated)	$1.70 \times 10^2$	2.06	-0.61	$2.00 \times 10^{-4}$
Device_P (red light)	$6.62 \times 10^1$	1.90	-0.29	$3.81 \times 10^{-4}$
Device_P (Nonirradiated)	$1.08 \times 10^2$	1.70	-0.54	$2.23 \times 10^{-4}$
Device_P (green light)	$1.73 \times 10^2$	1.72	-0.25	$3.12 \times 10^{-4}$
Device_P (Nonirradiated)	$5.43 \times 10^2$	1.90	-0.38	$1.56 \times 10^{-4}$
Device_P (blue light)	$1.62 \times 10^1$	4.67	0.66	$7.65 \times 10^{-5}$
Device_T (Nonirradiated)	$4.93 \times 10^3$	0.46	0.76	$6.40 \times 10^{-3}$
Device_T (red light)	$2.26 \times 10^2$	1.32	-0.12	$1.31 \times 10^{-2}$
Device_T (Nonirradiated)	$1.85 \times 10^3$	0.51	0.75	$5.41 \times 10^{-3}$
Device_T (green light)	$5.84 \times 10^1$	30.23	-2.61	$8.06 \times 10^{-3}$
Device_T (Nonirradiated)	$1.52 \times 10^3$	0.75	0.65	$1.21 \times 10^{-2}$

Device\_T (blue light)       $1.44 \times 10^2$       3.13      -2.33       $7.39 \times 10^{-3}$

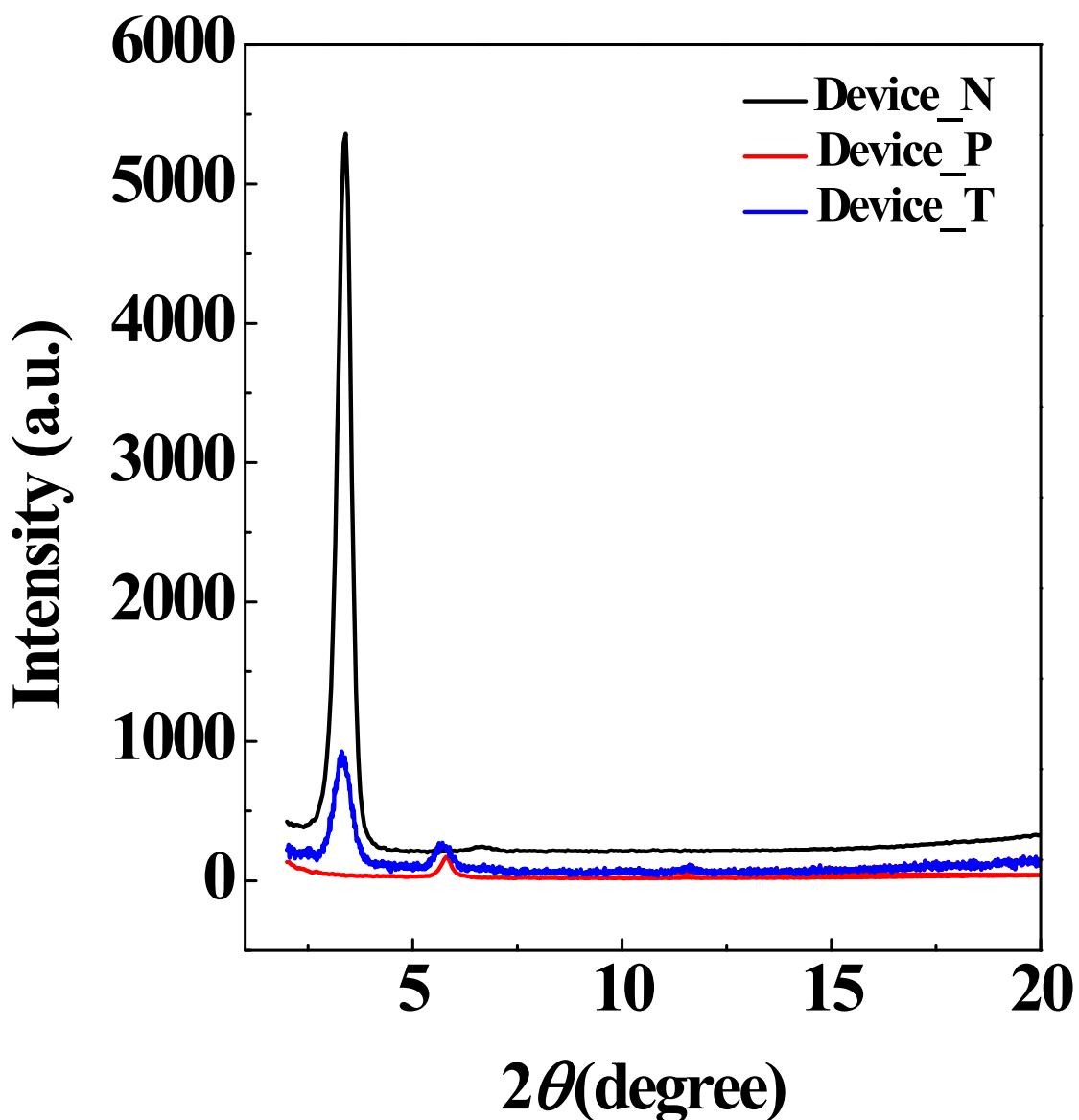
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**Table S3.** Summary of the performance parameters of organic thin-film phototransistors.

Material	Semiconductor	Voltage (V)	Light	P	R (A/W)	Ref.
EHPDI	N-type	80	White	5.44	$24.5 \times 10^{-3}$	34
CV/NaBH <sub>4</sub> -doped BPE-PTCDI	N-type	100	polychromatic	6	89.03	35
diF-TES ADT	p-type	-40	Green	115	0.139	36
TIPS-pentacene	p-type	-10	blue	$\sim 4 \times 10^4$	$17 \times 10^{-3}$	37
(PDPPT3-HDO): COTIC-4F	heterojunction structure	$\pm 3$	UV light	$1.3 \times 10^5$	$1.07 \times 10^{-3}$	38
PTCDI-C <sub>13</sub>	N-type	3	Green	301.22	$0.12 \times 10^{-3}$	This work
Pentacene	P-type	3	Red	17.03	$0.01 \times 10^{-3}$	This work
PTCDI-C <sub>13</sub> /Pentacene (6 layer)	heterojunction structure	$\pm 3$	Green	5007.70	$8.36 \times 10^{-3}$	This work



**Fig. S1** The capacitance values of the  $\text{AlO}_x$  and  $\text{PI}/\text{AlO}_x$  dielectric layers at a measurement frequency of 1 kHz.



**Fig. S2.** XRD diffraction patterns of different semiconductor devices.